L Number	Hits	Search Text	DB	Time stamp
1	41	(ferroelectric ferro-electric FeRAM) and (program$4 writ$3) and (chang$3 with polar$7 with (volt$3 near3 gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/19 15:47
2	8	(ferroelectric ferro-electric FeRAM) and ((program$4 writ$3) same (chang$3 with polar$7 with (film layer) with (volt$3 near3 gate)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/19 15:48
-	207	(mfs MFMIS) with (ferroelectric ferro-electric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 12:44
-	109	((mfs MFMIS) with (ferroelectric ferro-electric)) and (writ$3 program$4) and (read$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:59
-	12	(((mfs MFMIS) with (ferroelectric ferro-electric)) and (writ$3 program$4) and (read$3)) and ((current adj3 chang$3) same (Vds voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:58
-	14498	(mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:06
-	3093	((mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)) and (writ$3 program$4) and (read$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:08
-	29	(((mfs MFMIS) (metal adj4 (ferroelectric ferro-electric) adj4 insulator)) and (writ$3 program$4) and (read$3)) and ((current adj3 chang$3) same (Vds voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 12:55
-	18496	(mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:07
-	3302	((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ$3 program$4) and (read$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:09
-	29	(((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ$3 program$4) and (read$3)) and ((current adj3 chang$3) same (Vds voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:58
-	10	(((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ$3 program$4) and (read$3)) and ((current adj3 chang$3) same (Vds voltage)) and (ferroelectric adj3 capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:55
-	10	((((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ$3 program$4) and (read$3)) and ((current adj3 chang$3) same (Vds voltage)) and (ferroelectric adj3 capacitor)) and (gate adj3 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:55

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-	4	(((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3 insulator)) and (writ$3 program$4) and (read$3)) and ((current adj3 chang$3) same (Vds voltage)) and ((ferroelectric adj3 capacitor) with (gate adj3 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 17:00
-	205	((ferroelectric adj3 capacitor) with (gate adj3 electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:58
-	40	(((ferroelectric adj3 capacitor) with (gate adj3 electrode))) and (mfs MFIS MFMIS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 16:58
-	32	((((ferroelectric adj3 capacitor) with (gate adj3 electrode))) and (mfs MFIS MFMIS)) and (writ$3 program$4) and (read$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 17:00
-	16	(((((ferroelectric adj3 capacitor) with (gate adj3 electrode))) and (mfs MFIS MFMIS)) and (writ$3 program$4) and (read$3)) and ((ferroelectric ferro-electric) adj3 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/06 17:00
-	5690	read$3 same ((voltage potential bias) with drain with source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:17
-	574	((unsaturat$3 non-saturat$3) near3 region) and (saturat$3 near3 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:17
-	22	(((unsaturat$3 non-saturat$3) near3 region) and (saturat$3 near3 region)) and (nonvolatile non-volatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:19
-	2835	(read$3 same ((voltage potential bias) with drain with source)) and (nonvolatile non-volatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:20
-	5	((((unsaturat$3 non-saturat$3) near3 region) and (saturat$3 near3 region)) and (nonvolatile non-volatile)) and ((read$3 same ((voltage potential bias) with drain with source)) and (nonvolatile non-volatile))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:23
-	124614	((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:25
-	22	(((unsaturat$3 non-saturat$3) near3 region) and (saturat$3 near3 region)) and (((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:25
-	1	((((unsaturat$3 non-saturat$3) near3 region) and (saturat$3 near3 region)) and (((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile)) and ((read$3 with data with (appl$3 near3 (voltage bias potential)) with source with drain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:27

-	1	(((unsaturat$3 non-saturat$3) near3 region) and (saturat$3 near3 region)) and ((read$3 with data with (appl$3 near3 (voltage bias potential)) with source with drain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:27
-	224	(read$3 with data with (appl$3 near3 (voltage bias potential)) with source with drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:30
-	181	(((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile) and ((read$3 with data with (appl$3 near3 (voltage bias potential)) with source with drain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:16
-	1	(((unsaturat$3 non-saturat$3) near3 region) and (saturat$3 near3 region)) and ((((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile) and ((read$3 with data with (appl$3 near3 (voltage bias potential)) with source with drain)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:29
-	1669	read$3 same ((appl$3 near3 (voltage bias potential)) with source with drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:33
-	3	(((unsaturat$3 non-saturat$3) near3 region) and (saturat$3 near3 region)) and (read$3 same ((appl$3 near3 (voltage bias potential)) with source with drain))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:45
-	11	((unsaturat$3 non-saturat$3) near3 region) with read$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:53
-	1	(((unsaturat$3 non-saturat$3) near3 region) with read$3) and (non-volatile nonvolatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:52
-	3769	(unsaturat$3 non-saturat$3) with read$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:53
-	3779	(unsaturat$3 non-saturat$3 nonsaturat$3) with read$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:53
-	200	((unsaturat$3 non-saturat$3 nonsaturat$3) with read$3) and (non-volatile nonvolatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 11:54
-	200	(((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile) and (((unsaturat$3 non-saturat$3 nonsaturat$3) with read$3) and (non-volatile nonvolatile))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:04
-	28	((((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile) and (((unsaturat$3 non-saturat$3 nonsaturat$3) with read$3) and (non-volatile nonvolatile))) and (read reading)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:09

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-	8	(((((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile nonvolatile) and (((unsaturat$3 non-saturat$3 nonsaturat$3) with read$3) and (non-volatile nonvolatile))) and (read reading)) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:09
-	1	((read$3 with data with (appl$3 near3 (voltage bias potential)) with source with drain)) and ((unsaturat$3 non-saturat$3 nonsaturat$3) near3 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:19
-	1	read$3 with (unsaturat$3 non-saturat$3 nonsaturat$3) with (current near3 detect$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 12:20